High Directivity

Monolithic Amplifier

0.5-2.5 GHz

Product Features

- 2.8V & 5V operation
- Micro-miniature size .120"X.120"
- Internal DC blocking at RF input and output
- High directivity, 20 dB typ.
- Low noise figure
- Output power, up to +17.9 dBm typ.
- Excellent repeatability
- Low cost
- Aqueous washable





MNA-2

CASE STYLE: DQ849

Typical Applications

- Buffer amplifier
- Cellular
- PCN
- · Communications satellite
- Defense

+RoHS Compliant

The +Suffix identifies RoHS Compliance. See our web site for RoHS Compliance methodologies and qualifications

NO LONGER AVAILABLE,

General Description

MNA-2 is a wideband amplifier offering high dynamic range. It has repeatable performance from lot to lot. It is enclosed in a 3x3 mm MCLP plastic package. MNA-2 is fabricated using GaAs MESFET technology. Expected MTBF at 85°C case temperature is 50,000 years at 2.8V; 8,000 years at 5V.

Function	Pin Number	Description	
RF IN	2	RF input pin	
RF-OUT	5	RF output pin	
DC	7, with 1000 pf	bypass to ground; connect pin 8 via 33 ohms to pin 7 externally	Bias pins
GND	3,4 and paddle in center of bottom Connections to ground		Connections to ground
OPTIONAL	1,6	No internal connection; recommended use: per PCB Layout PL-078	



Electrical Specifications at 25°C

Parameter		Min.	Ту	p.	Max.	Units
Frequency Range		0.5			2.5	GHz
at DC Volts		5.0	5.0	2.8	5.0	V
Gain	f=0.5 GHz		10.6	9.6		dB
	f=1.0 GHz		12.8	11.5		
	f=1.5 GHz		12.8	11.2		
	f=2.0 GHz	10.3	12.3	10.7		
	f=2.5 GHz		11.9	10.2		
Input Return Loss f=0.	75-2.5 GHz		14	14		dB
Output Return Loss f=0.	75-2.5 GHz		12.5	12.5		dB
Output Power @ 1 dB compression	f=0.5 GHz		17.7	12.9		dBm
NO LONG	f=2.5GHz	Λ\/ /	17.9	12.4	DI E	
Outsut IDO	f=1 GHz	AV	26.5	23.2	PLE	J dBm
Output IP3	f=2 GHz		28.0	24.2		
Noise Figure REPLACEIVE	f=1 GHz	MO	5	.4	VINA	dB
Directivity (Isolation - Gain) f=0).5-2.5 GHz		2	0		
DC Current			76	60	95	mA
Thermal Resistance, junction-to-case			7	8		°C/W

Absolute Maximum Ratings

Parameter	Ratings			
Operating Temperature	-40°C to 85°C			
Storage Temperature	-55°C to 100°C			
DC Voltage	7V at pin 7 10V at pins 2 & 5			
Power Dissipation	500mW			

Note: Permanent damage may occur if any of these limits are exceeded. These ratings are not intended for continuous normal operation.



Product Marking



Additional Detailed Technical Information

Additional information is available on our web site. To access this information enter the model number on our web site home page.

Performance data, graphs, s-parameter data set (.zip file)

Case Style: DQ849

Plastic package, exposed paddle, lead finish: tin/lead

Tape & Reel: F104

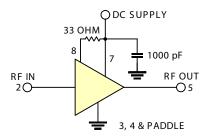
Standard quantities available on reel: 7" reels with 20, 50, 100, 200, 500, 1K, or 2K devices.

Suggested Layout for PCB Design: PL-078 ENT MODEL MNA-2+

Evaluation Board: TB-186+

Environmental Ratings: ENV08T1

Recommended Application Circuit



For detailed performance specs & shopping online see web site

Visual

ESD Rating

Human Body Model (HBM): Class 1A (250v to < 500v) in accordance with ANSI/ESD STM 5.1 - 2001

Charged Device Model (CDM): Class III (500 to 1000v) in accordance with JESD22-C101A

MSL Rating

Moisture Sensitivity: MSL1 in accordance with IPC/JEDEC J-STD-020C

No.	Test Required	Condition	Standard	Quantity
1	Visual Inspection	Low Power Microscope Magnification 40x	MIP-IN-0003 (MCT spec)	10 units
2	Electrical Test	Room Temperature	SCD (MCL spec)	10 units
3	SAM Analysis	Less than 10% growth in term of delamination	J-Std-020C (Jedec Standard)	10 units
4	Moisture Sensitivity Level 1	Bake at 125°C for 24 hours Soak at 85°C/85%RH for 168 hours Reflow 3 cycles at 260°C peak	J-Std-020C (Jedec Standard)	10 units
		NO LONGEF	RAVA	LABI

MSL Test Flow Chart DDEL MNA-2+ Visual Electrical Test SAM Analysis Start Inspection Soak Reflow 3 cycles, Bake at 125°C, 85°C/85RH 260°C 24 hours 168 hours

SAM Analysis

Electrical Test